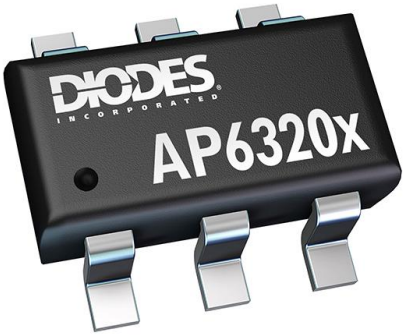
DMN2024UVT-13 Datasheet



DiGi Electronics Part Number	DMN2024UVT-13-DG
Manufacturer	Diodes Incorporated
Manufacturer Product Number	DMN2024UVT-13
Description	MOSFET 2N-CH 20V 7A TSOT23-6
Detailed Description	Mosfet Array 20V 7A (Ta) 1W Surface Mount TSOT-23-6

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
DMN2024UVT-13	Diodes Incorporated
Series:	Product Status:
-	Active
Technology:	Configuration:
MOSFET (Metal Oxide)	2 N-Channel (Dual) Common Drain
FET Feature:	Drain to Source Voltage (Vdss):
-	20V
Current - Continuous Drain (Id) @ 25°C:	Rds On (Max) @ Id, Vgs:
7A (Ta)	24mOhm @ 6.5A, 4.5V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
900mV @ 250µA	7.1nC @ 4.5V
Input Capacitance (Ciss) (Max) @ Vds:	Power - Max:
647pF @ 10V	1W
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
SOT-23-6 Thin, TSOT-23-6	TSOT-23-6
Base Product Number:	
DMN2024	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

Lead-free Green

DMN2024UVT

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D T_A = +25°C
20V	24mΩ @ V_{GS} = 4.5V	7A
	28mΩ @ V_{GS} = 2.5V	5A

Features and Benefits

- Low On-Resistance
- Low-Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q101, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.**
- **https://www.diodes.com/quality/product-definitions/**

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

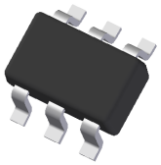
Applications

- Backlighting
- DC-DC Converters
- Power Management Functions

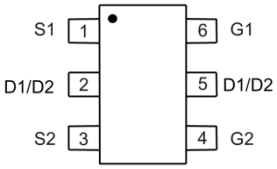
Mechanical Data

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish—Matte Tin Annealed Over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.013 grams (Approximate)

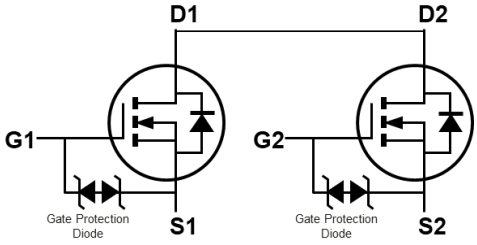
ESD Protected Gate



TSOT26



Top View



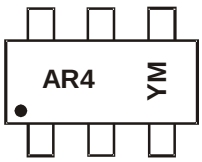
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2024UVT-7	TSOT26	3000/Tape & Reel
DMN2024UVT-13	TSOT26	10,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



AR4 = Product Type Marking Code
YM = Date Code Marking
Y or $\overline{Y}$ = Year (ex: G = 2019)
M = Month (ex: 9 = September)

Date Code Key

Year	2018	2019	2020	2021	2022	2023	2024	2025
Code	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±10	V
Continuous Drain Current (Note 6) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	7.0 5.0	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	2.3	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	35	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	1.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\Theta JA}$	124	°C/W
Total Power Dissipation (Note 6)		P_D	1.6	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\Theta JA}$	78	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	1.0	µA	V_{DS} = 20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.5	—	0.9	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	19	24	mΩ	V_{GS} = 4.5V, I_D = 6.5A
			22	28		V_{GS} = 2.5V, I_D = 5.5A
			25	34		V_{GS} = 1.8V, I_D = 3.5A
Diode Forward Voltage	V_{SD}	—	0.9	1.2	V	V_{GS} = 0V, I_D = 5A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	647	—	pF	V_{DS} = 10V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	78	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	38	—	pF	
Gate Resistance	R_g	—	628	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	7.1	—	nC	V_{GS} = 4.5V, V_{DS} = 10V, I_D = 6.5A
Gate-Source Charge	Q_{gs}	—	0.9	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.7	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	98	—	ns	V_{DS} = 10V, V_{GS} = 4.5V, R_L = 10Ω, R_G = 6Ω, I_D = 1A
Turn-On Rise Time	t_R	—	140	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	1024	—	ns	
Turn-Off Fall Time	t_F	—	434	—	ns	
Reverse Recovery Time	t_{RR}	—	245	—	ns	I_F = 1.0A, di/dt = 100A/µs
Reverse Recovery Charge	Q_{RR}	—	149	—	nC	I_F = 1.0A, di/dt = 100A/µs

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
6. Device mounted on 1" × 1" FR-4 PCB with high-coverage 2oz. copper, single sided.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

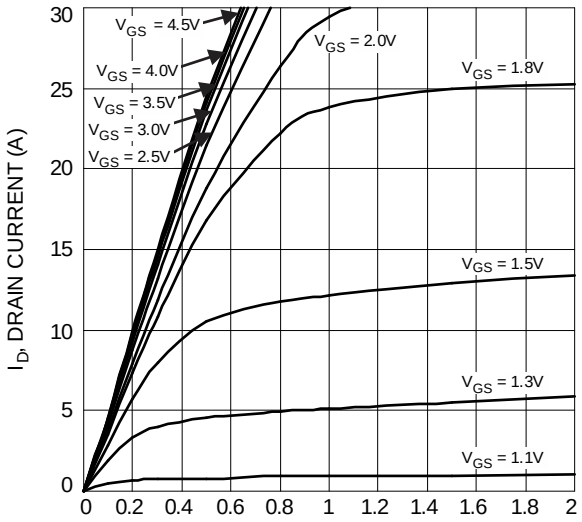


Figure 1 Typical Output Characteristic

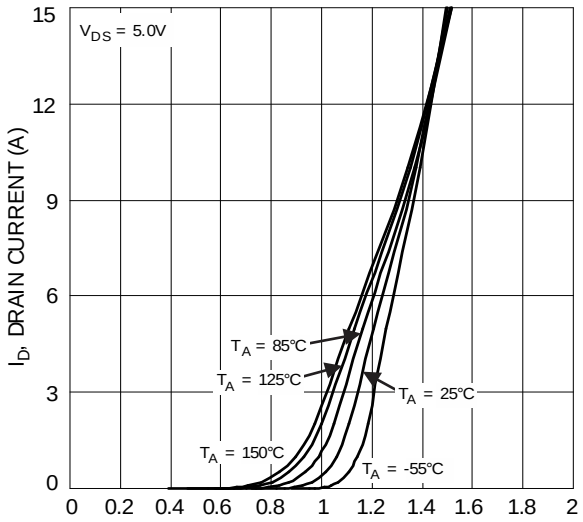


Figure 2 Typical Transfer Characteristics

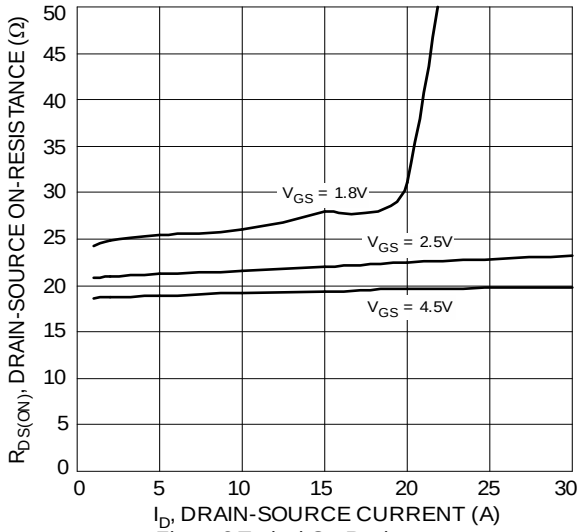


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

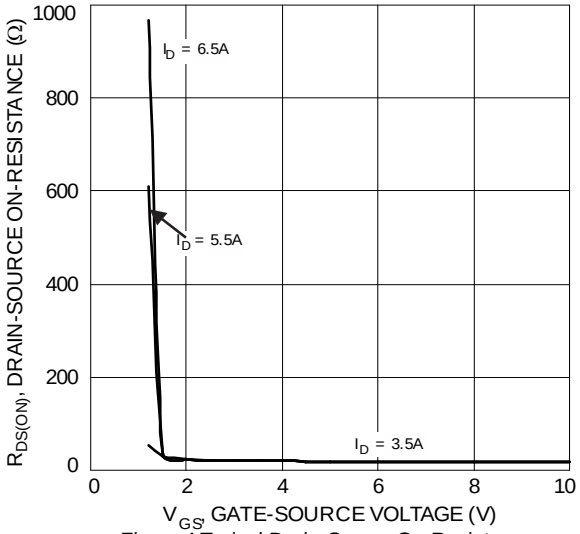


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

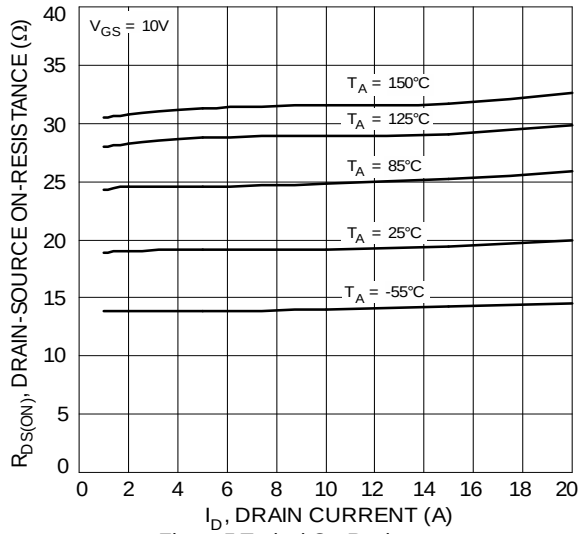


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

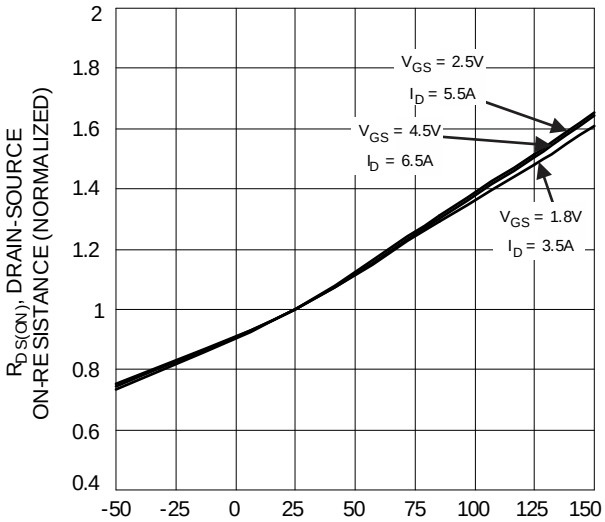


Figure 6 On-Resistance Variation with Temperature

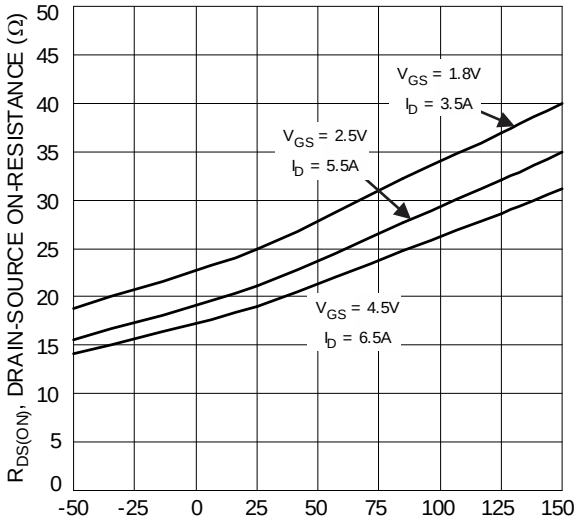


Figure 7 On-Resistance Variation with Temperature

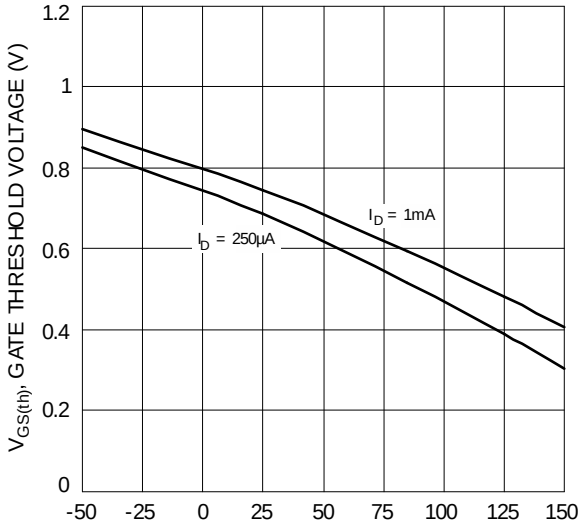


Figure 8 Gate Threshold Variation vs. Junction Temperature

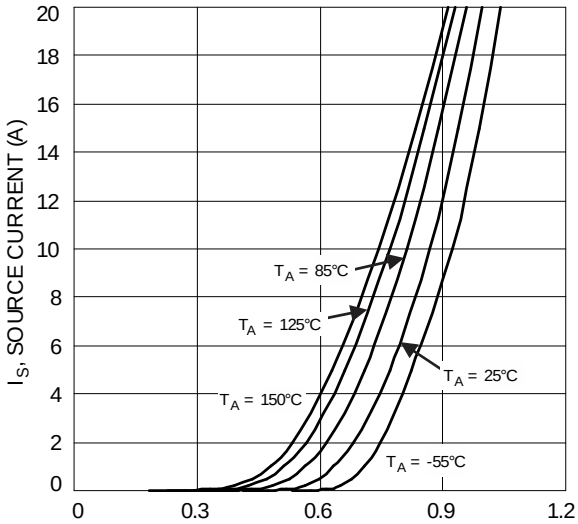


Figure 9 Diode Forward Voltage vs. Current

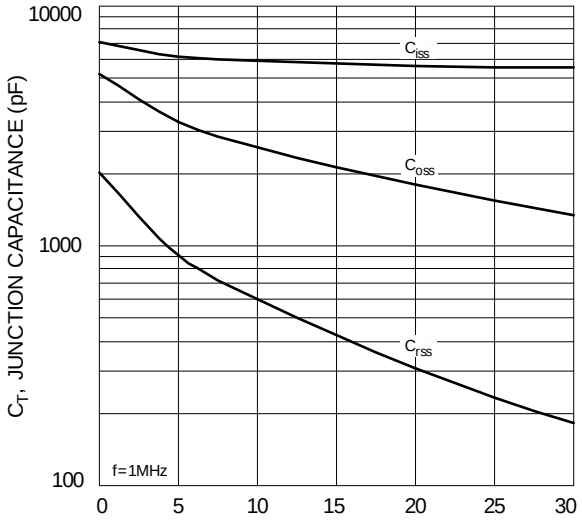


Figure 10 Typical Junction Capacitance

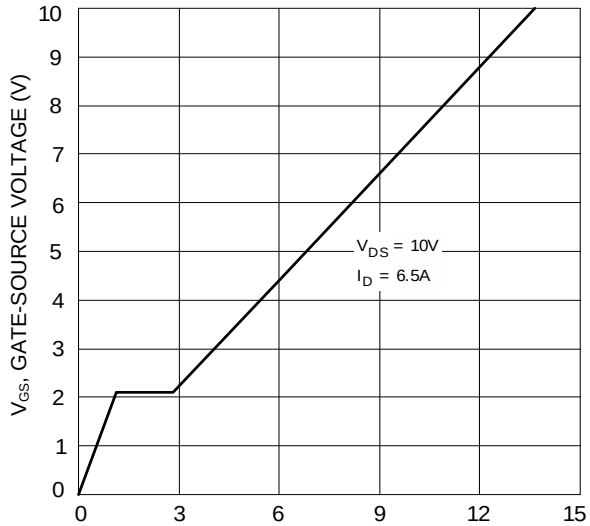


Figure 11 Gate Charge

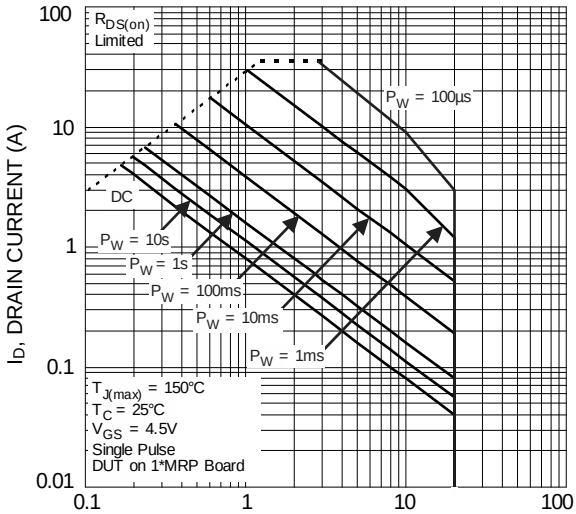


Figure 12 SOA, Safe Operation Area

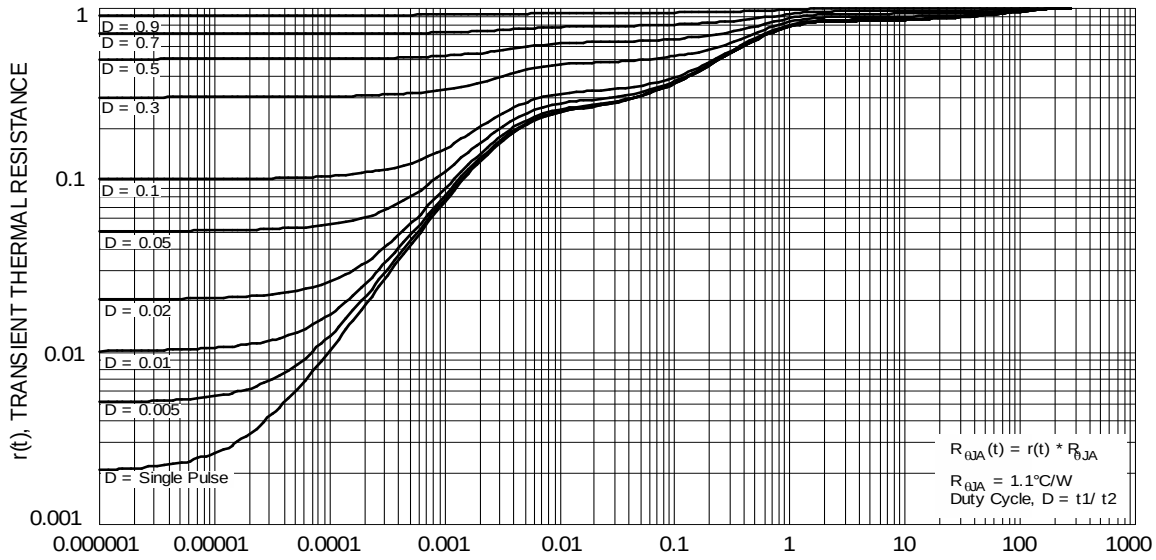
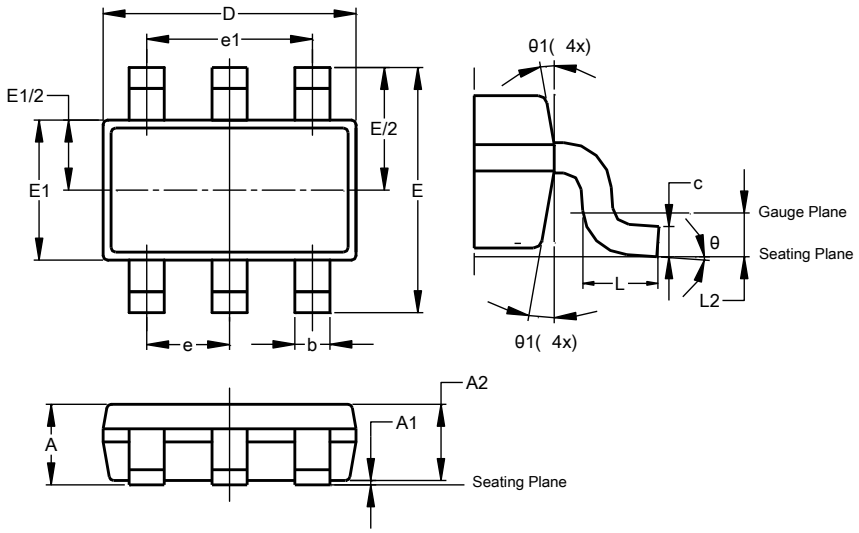


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26

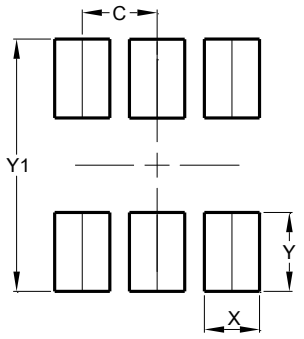


TSOT26			
Dim	**Min**	**Max**	**Typ**
A	–	1.00	–
A1	0.010	0.100	–
A2	0.840	0.900	–
D	2.800	3.000	2.900
E	2.800 BSC		
E1	1.500	1.700	1.600
b	0.300	0.450	–
c	0.120	0.200	–
e	0.950 BSC		
e1	1.900 BSC		
L	0.30	0.50	–
L2	0.250 BSC		
θ	0°	8°	4°
θ1	4°	12°	–
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199

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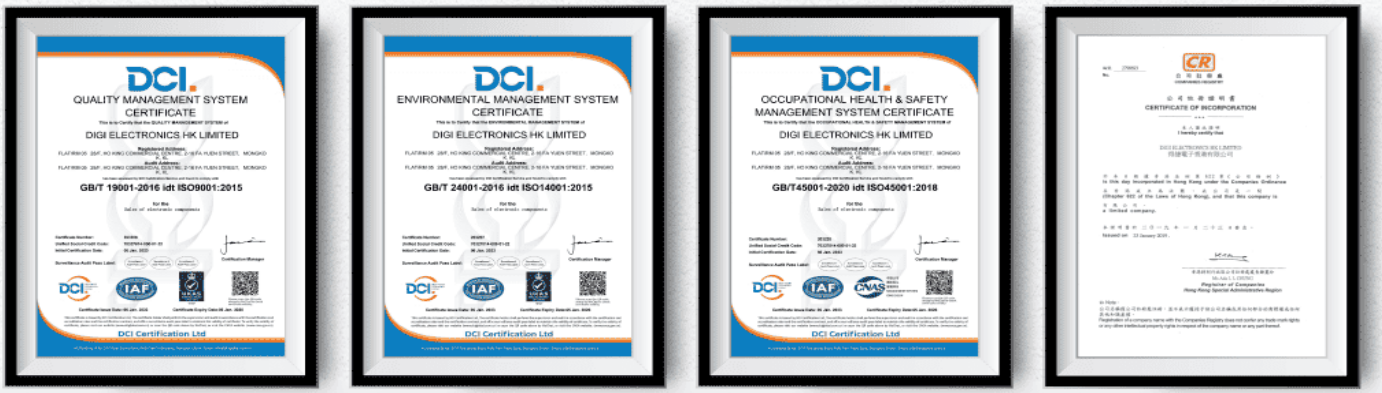

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